

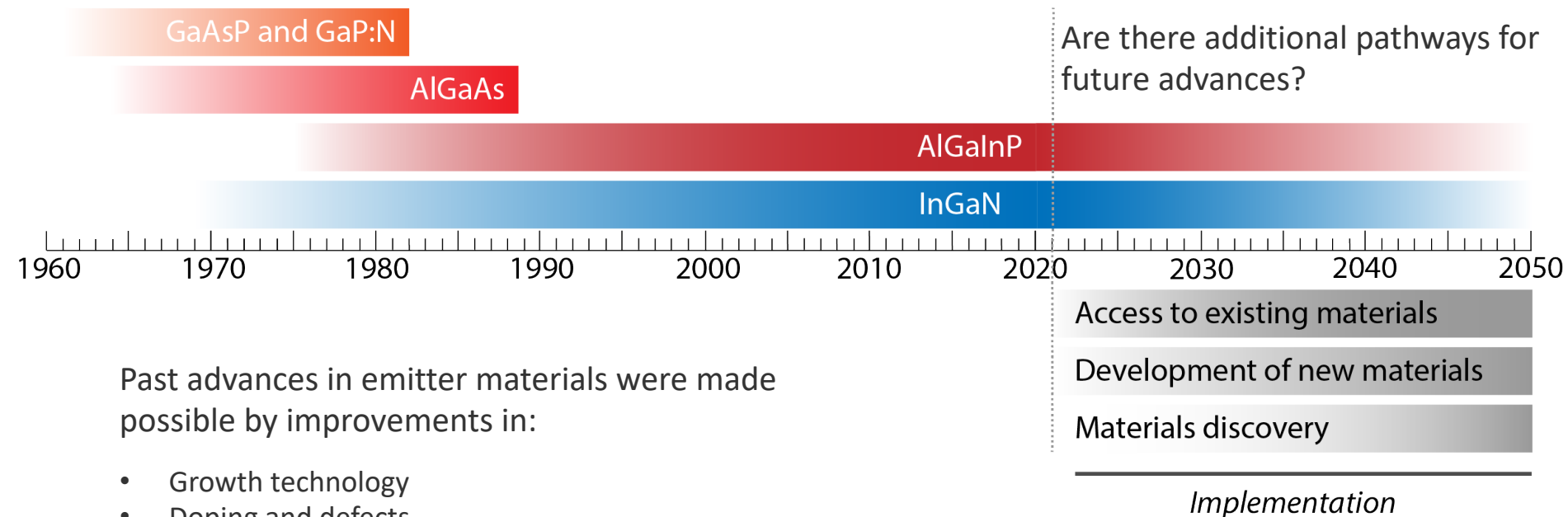
# Leveraging Capabilities for Improving Emitter Materials

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# Pathways for Emitter Material Improvements



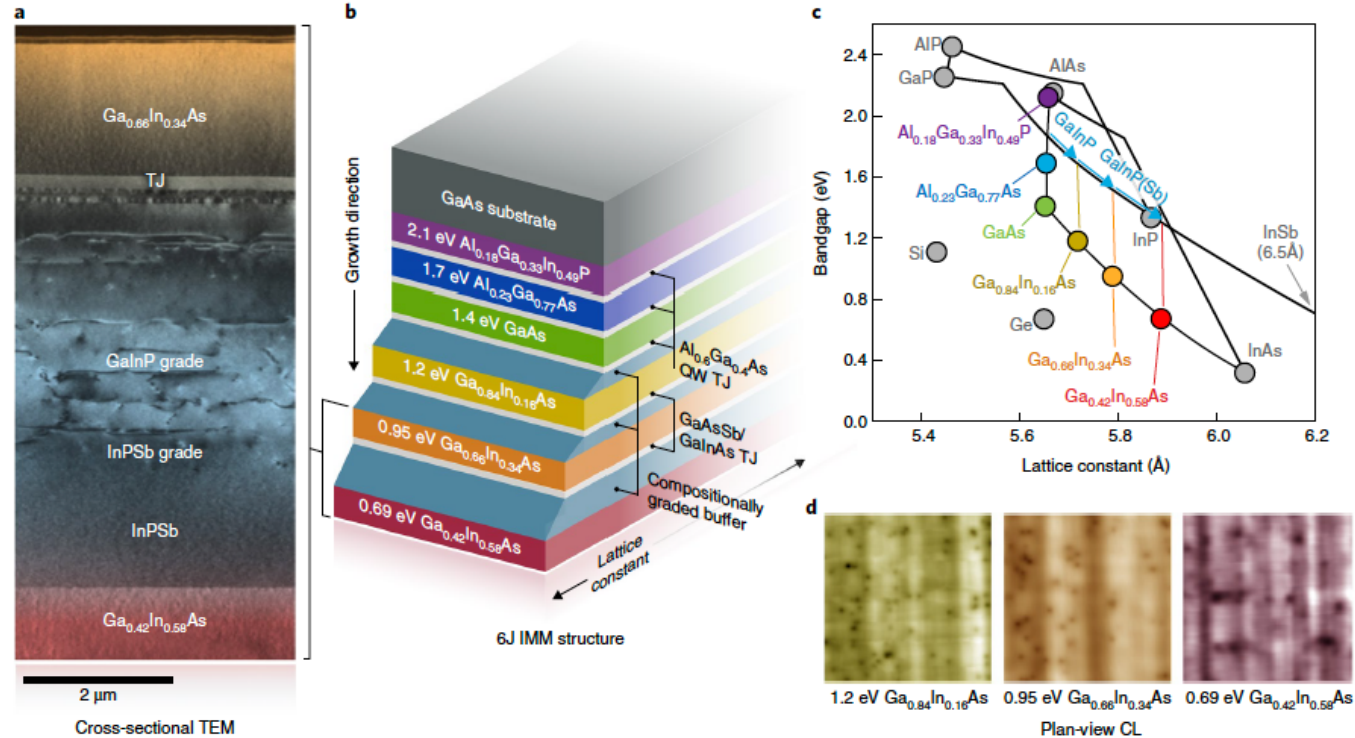
Historical emitter material timeline data adapted from:

R.D. Dupuis and M.R. Krames, History, Development and Applications of High-Brightness Visible Light-Emitting Diodes, *J. Lightwave Technology*, **26**, 1154 (2008)

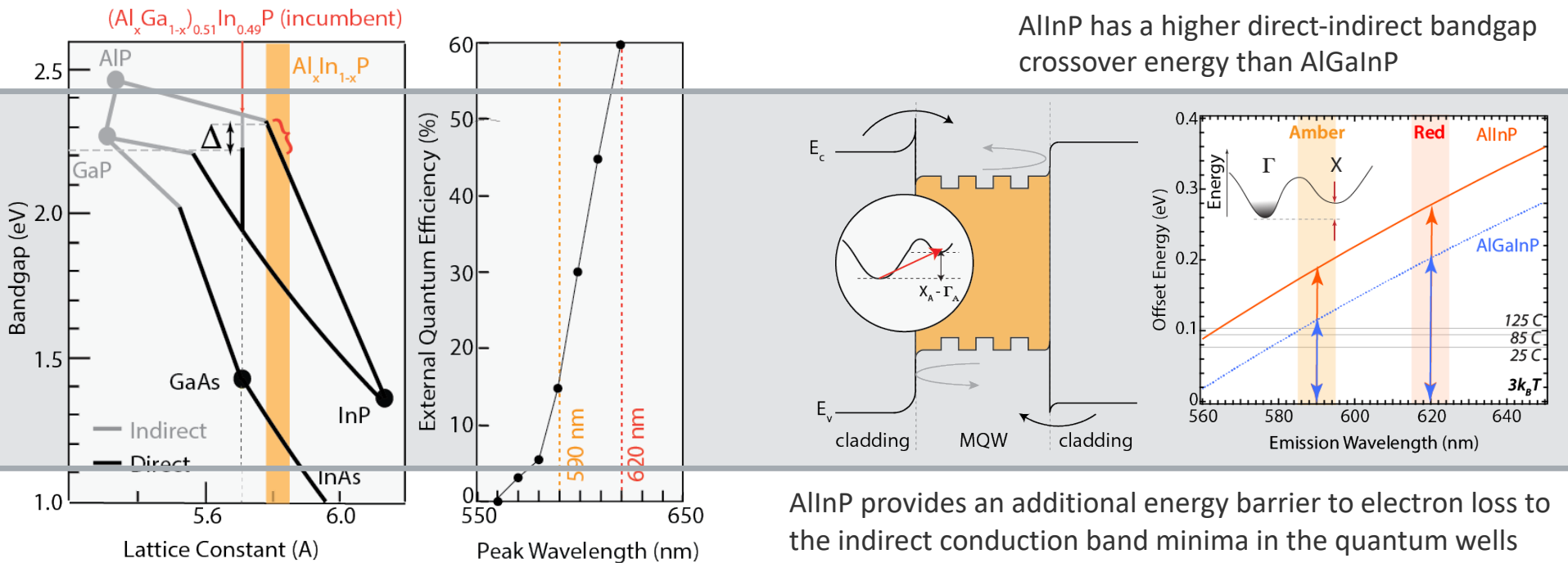
S. Nakamura and M.R. Krames, History of Gallium-Nitride-Based Light-Emitting Diodes for Illumination, *Proc. of the IEEE*, **101**, 2211 (2013)

# Accessing Existing Materials: High Efficiency Photovoltaics

Multijunction solar cells have advanced on the ability to access and integrate III-V semiconductors through metamorphic growth.

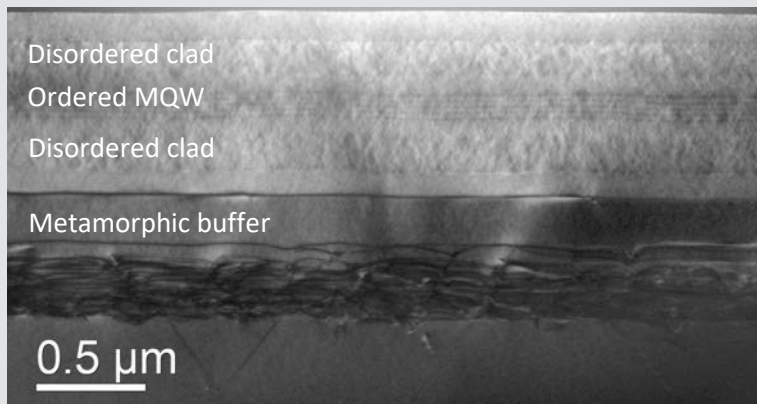


# Example: Direct Bandgap AlInP for Red and Amber LEDs



# Example: Direct Bandgap AlInP for Red and Amber LEDs

Ordered/disordered AlInP LEDs can be grown on GaAs substrates with manageable dislocation densities.



TEM and diffraction images by N. Pokharel and P. Ahrenkiel (SDSMT)

LED growth by MicroLink Devices Inc.

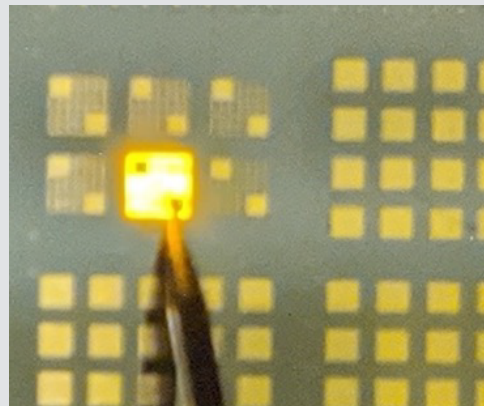
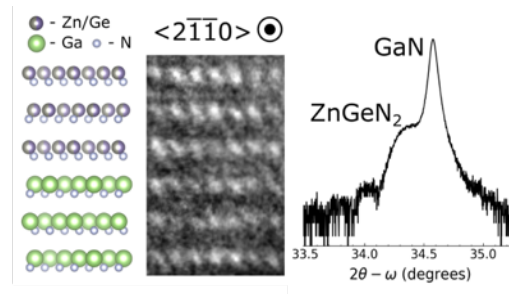
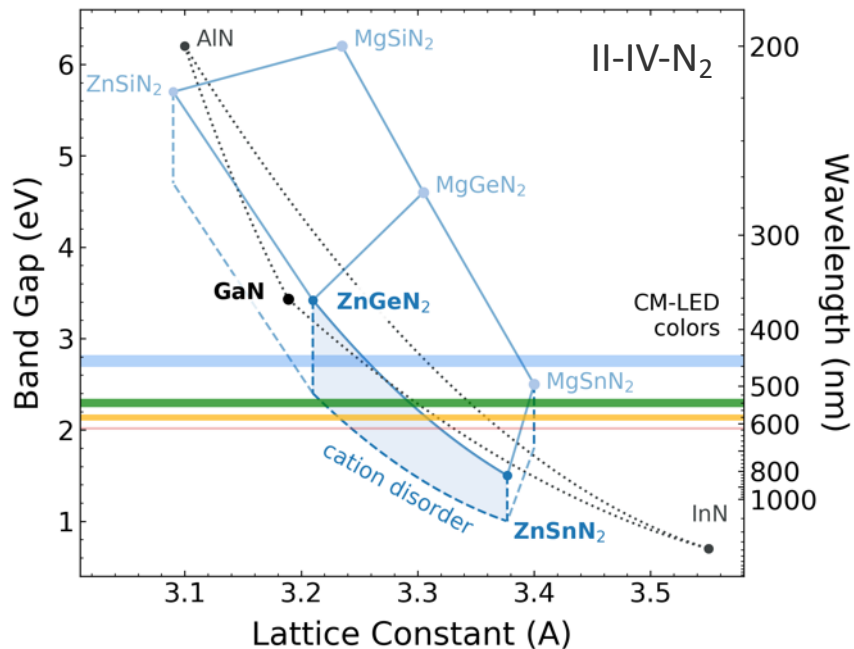


Photo by K. Alberi, NREL

LEDs have been demonstrated, but there is still a lot of room for improvement.

# Developing Known “New” Materials: Ternary Nitrides



Many less-studied ternary nitrides have suitable bandgaps for visible light emission and can be integrated with GaN

- Disorder based tunability of band gap
- Non-polar options
- Alloying can fill in bandgap and lattice constant space

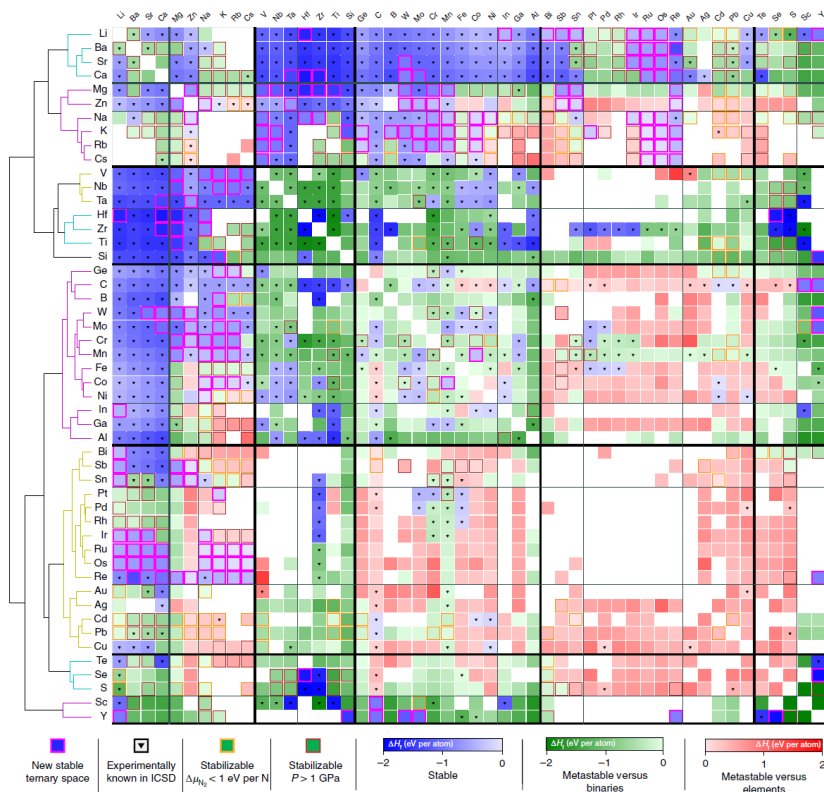
R.R. Schnepf, *et al.*, Utilizing site disorder in the development of new energy-relevant semiconductors, *ACS Energy Lett.*, **5**, 2027 (2020)

M. Brooks Tellekamp, *et al.*, Heteroepitaxial integration of ZnGeN<sub>2</sub> on GaN buffers using molecular beam epitaxy, *Crystal Growth and Design*, **20**, 1868 (2020)

*Ternary Nitrides: Fundamentals and Emerging Device Applications*, A. L. Greenaway *et al.*, accepted (2020) – Annual Reviews of Materials Research

# Computational Materials Discovery

## Example: ternary nitrides



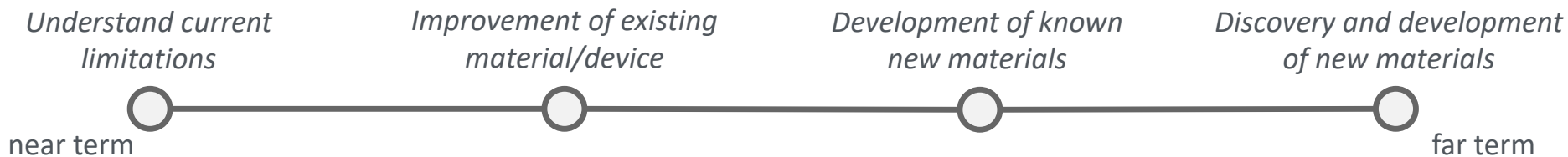
## Materials Discovery

- New compounds  
Composition and crystal structure, basic properties, synthesis
- Known compounds  
Identification of performance and application, how to make it work

## Materials Design

- Fine tuning of properties, often by alloying
- Composition-gradient thin-film synthesis

# Approaches and Considerations



## Existing Materials Improvement

- Build on previous R&D
- Learn from work performed by other industries
- May not be able to overcome fundamental material property limitations

## New Materials Development

- Expands materials selection
- Theory aids experimental materials optimization and hypothesis validation
- Longer development timeline

## Computational Materials Discovery

- Opportunities to identify materials with “optimal” properties
- Requires a lot of development
- Success is not assured
- Theoretical methods are still evolving



# Critical Questions for Implementation

*When do we shift the focus of R&D on emitter materials?*

- What timelines can the LED R&D community tolerate?
- What is an acceptable return on R&D investment?

*How can we leverage R&D for other technologies?*

- Build on breakthroughs in understanding and controlling material properties
- Collaboratively advance aspects that are beneficial to multiple technologies
- Engage a broader range of specialists

# Thank you

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